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Sommario/riassunto

This multi-contributor handbook discusses Molecular Beam Epitaxy (MBE), an epitaxial deposition technique which involves laying down layers of materials with atomic thicknesses on to substrates. It

summarizes MBE research and application in epitaxial growth with close discussion and a 'how to' on processing molecular or atomic beams that occur on a surface of a heated crystalline substrate in a vacuum. MBE has expanded in importance over the past thirty years (in terms of

unique authors, papers and conferences) from a pure research domain into commercial applications (prototype devi
